

# MOS FIELD EFFECT TRANSISTOR

# 2SJ607

## SWITCHING

## P-CHANNEL POWER MOS FET

### DESCRIPTION

The 2SJ607 is P-channel MOS Field Effect Transistor designed for high current switching applications.

### FEATURES

- Super low on-state resistance:  
 $R_{DS(on)1} = 11 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -42 \text{ A)}$   
 $R_{DS(on)2} = 16 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -42 \text{ A)}$
- Low input capacitance:  
 $C_{iss} = 7500 \text{ pF TYP. (} V_{DS} = -10 \text{ V, } V_{GS} = 0 \text{ V)}$
- Built-in gate protection diode

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Drain to Source Voltage ( $V_{GS} = 0 \text{ V}$ )	$V_{DS}$	-60	V
Gate to Source Voltage ( $V_{DS} = 0 \text{ V}$ )	$V_{GS}$	$\mp 20$	V
Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )	$I_{D(DC)}$	$\mp 83$	A
Drain Current (pulse) <sup>Note1</sup>	$I_{D(pulse)}$	$\mp 332$	A
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_T$	160	W
Total Power Dissipation ( $T_A = 25^\circ\text{C}$ )	$P_T$	1.5	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Avalanche Current <sup>Note2</sup>	$I_{AS}$	-50	A
Single Avalanche Energy <sup>Note2</sup>	$E_{AS}$	250	mJ

**Notes 1.**  $PW \leq 10 \mu\text{s}$ , Duty cycle  $\leq 1\%$

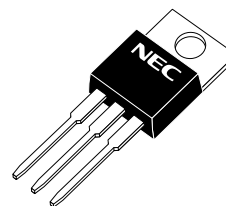
**2.** Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{DD} = -30 \text{ V}$ ,  $R_G = 25 \Omega$ ,  $V_{GS} = -20 \rightarrow 0 \text{ V}$

### ORDERING INFORMATION

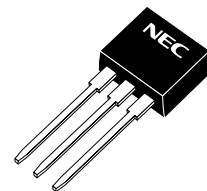
PART NUMBER	PACKAGE
2SJ607	TO-220AB
2SJ607-S	TO-262
2SJ607-ZJ	TO-263
2SJ607-Z	TO-220SMD <sup>Note</sup>

**Note** TO-220SMD package is produced only in Japan

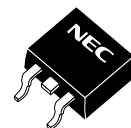
(TO-220AB)



(TO-262)



(TO-263, TO-220SMD)

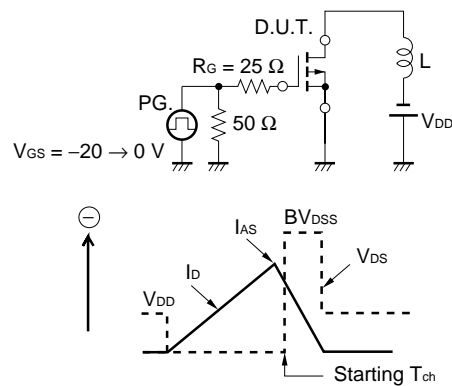


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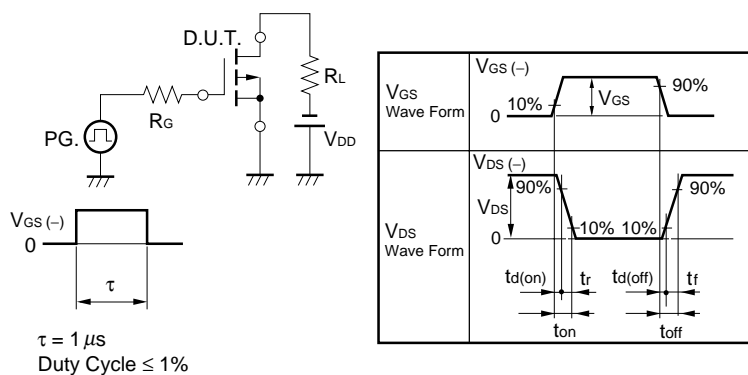
# ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V			-10	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μA
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-1.5	-2.0	-2.5	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -42 A	45	90		S
Drain to Source On-state Resistance	R <sub>DS(on)1</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -42 A		9.1	11	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -42 A		11	16	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V		7500		pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V		1800		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1 MHz		430		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -30 V, I <sub>D</sub> = -42 A		23		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = -10 V		16		ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 0 Ω		340		ns
Fall Time	t <sub>f</sub>			160		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = -48 V		188		nC
Gate to Source Charge	Q <sub>GS</sub>	V <sub>GS</sub> = -10 V		30		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = -83 A		48		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 83 A, V <sub>GS</sub> = 0 V		1.0		V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 83 A, V <sub>GS</sub> = 0 V		64		ns
Reverse Recovery Charge	Q <sub>rr</sub>	di/dt = 100 A/μs		150		nC

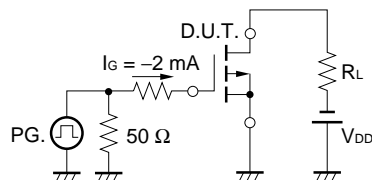
## TEST CIRCUIT 1 AVALANCHE CAPABILITY



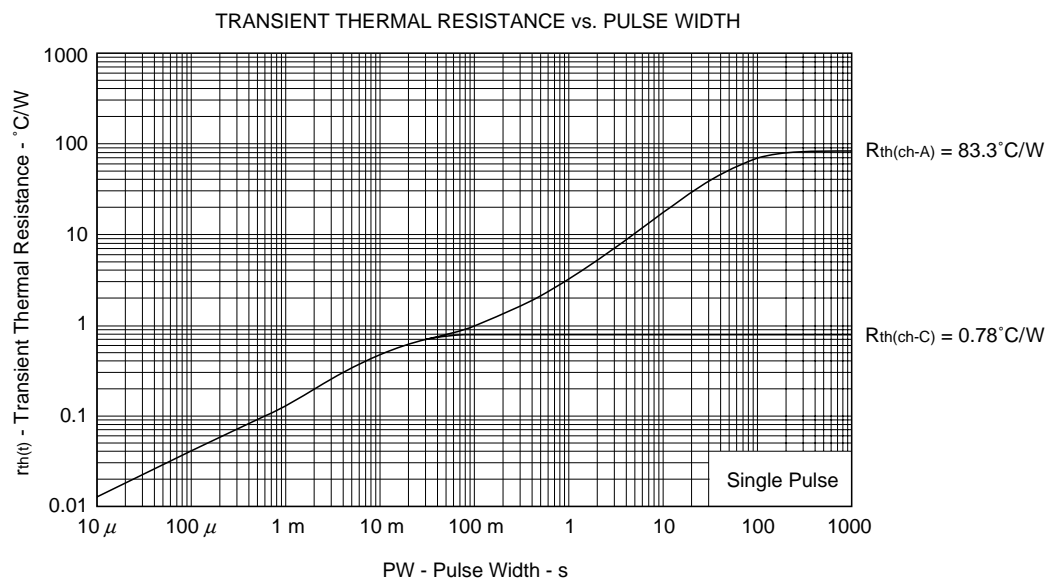
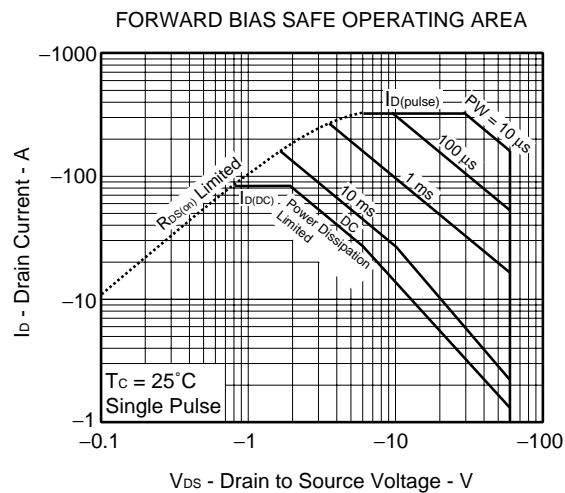
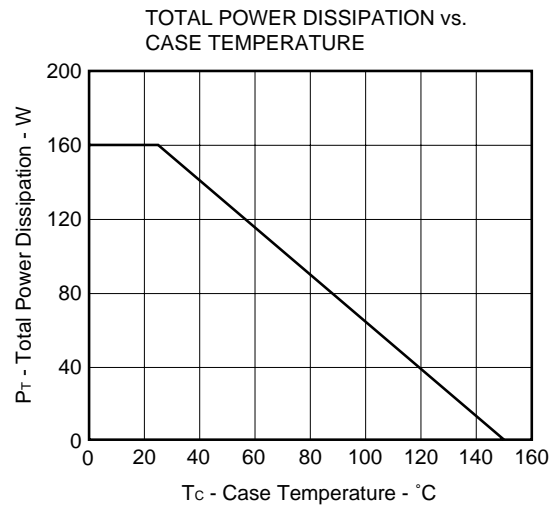
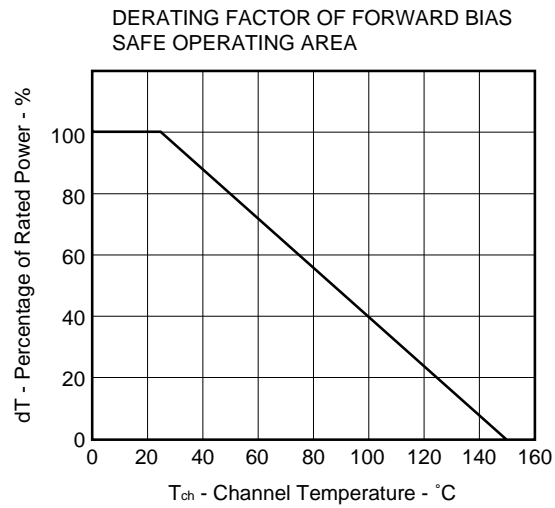
## TEST CIRCUIT 2 SWITCHING TIME



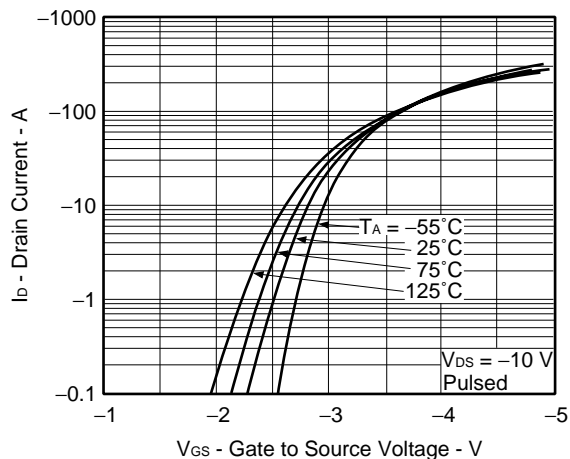
## TEST CIRCUIT 3 GATE CHARGE



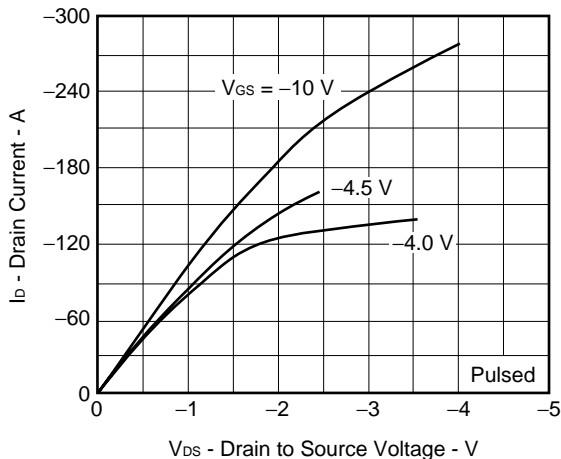
TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ )



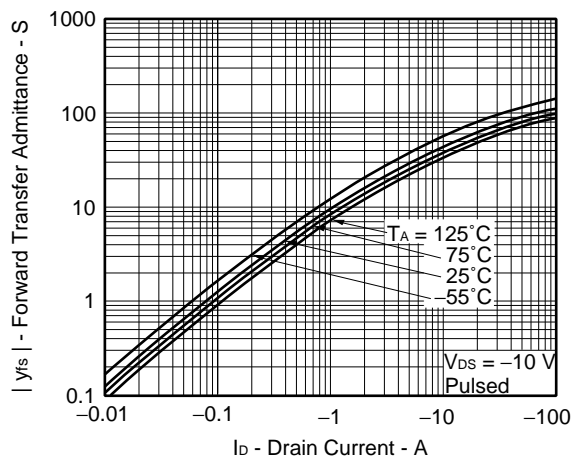
FORWARD TRANSFER CHARACTERISTICS



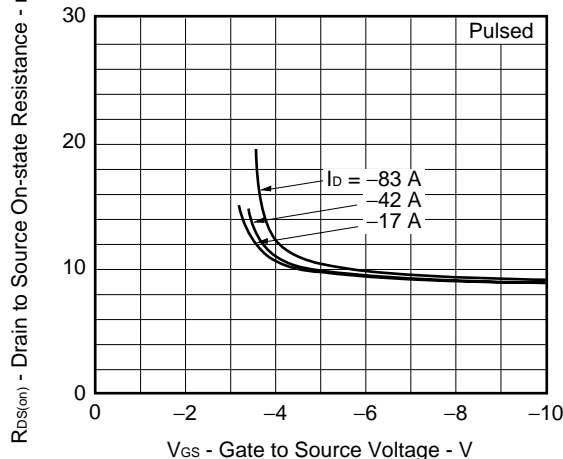
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



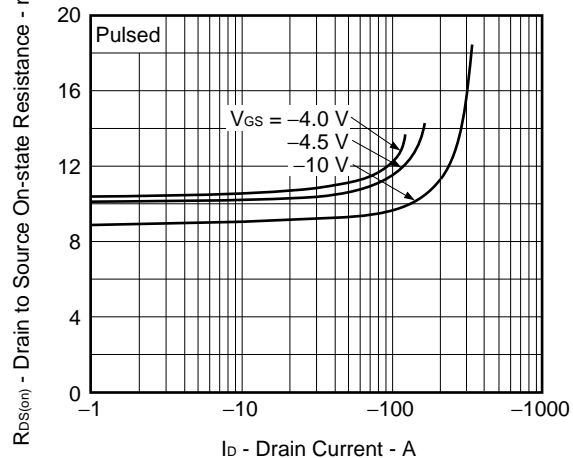
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



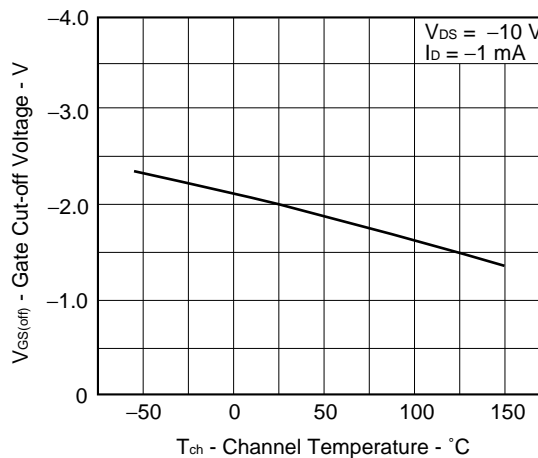
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



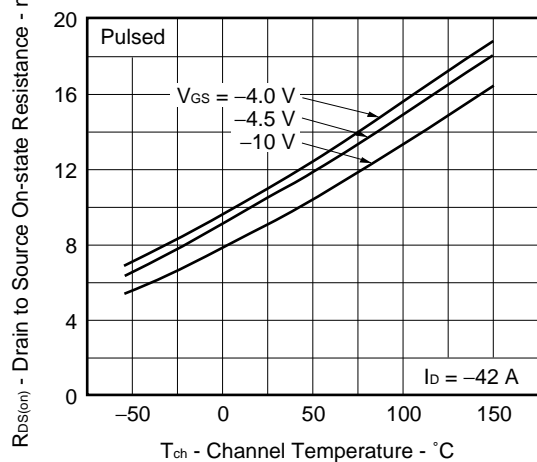
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



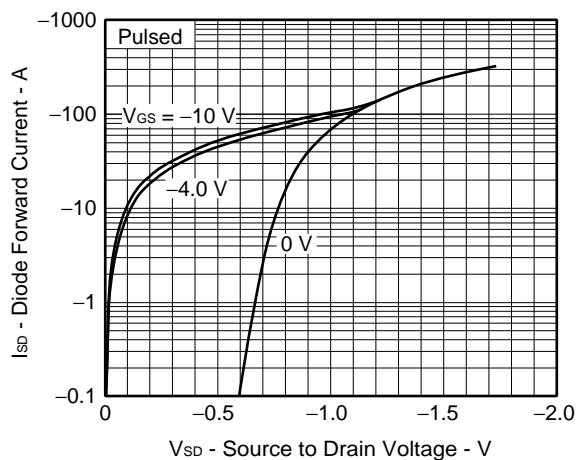
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



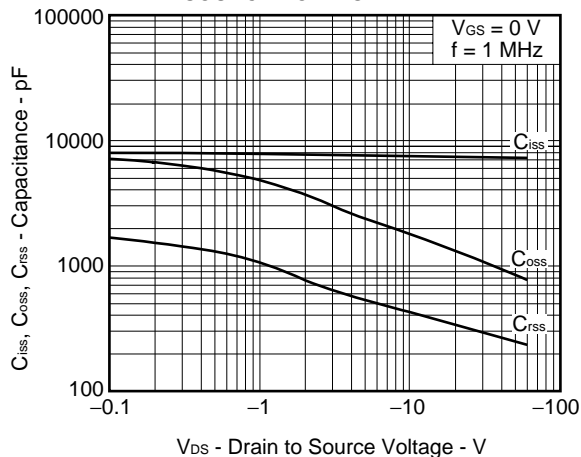
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



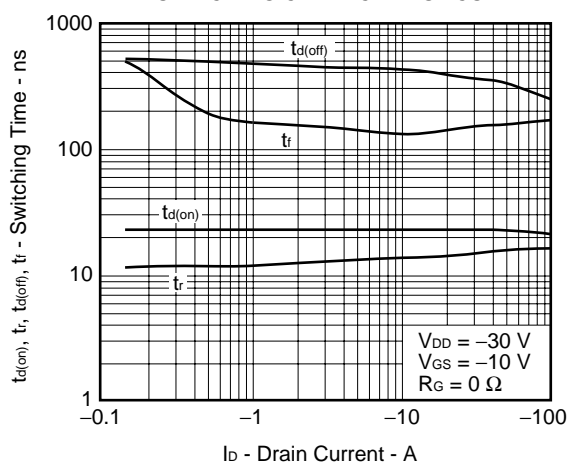
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



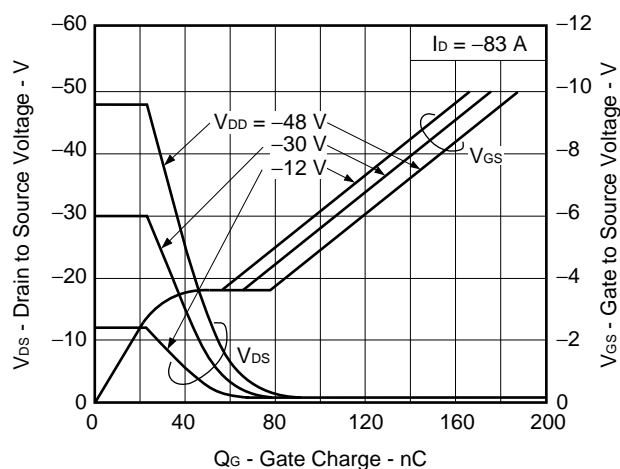
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



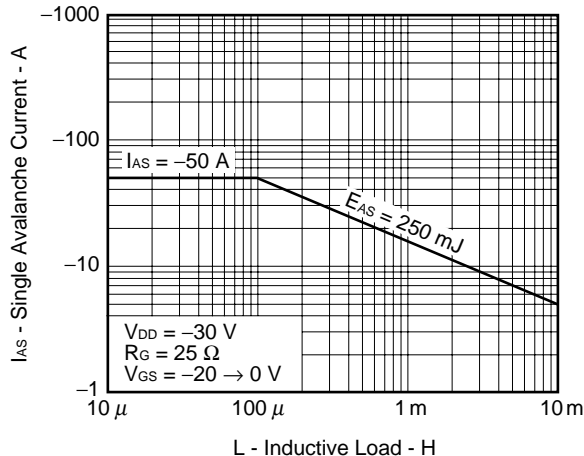
SWITCHING CHARACTERISTICS

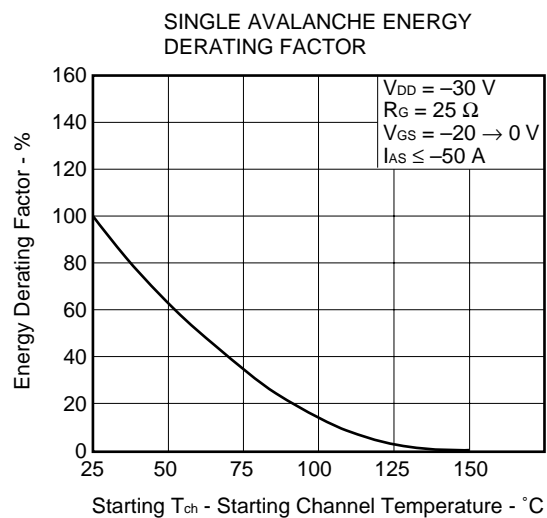


DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD







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